

ABSTRACT

Disclosed are semiconductor devices and methods of manufacturing the same. The semiconductor device comprises a first transistor on a substrate, and a second transistor on the substrate. Each of the first and second transistors includes a plurality of semiconductor patterns vertically stacked on the substrate and vertically spaced apart from each other, and a gate dielectric pattern and a work function pattern filling a space between the semiconductor patterns. The work function pattern of the first transistor includes a first work function metal layer, the work function pattern of the second transistor includes the first work function metal layer and a second work function metal layer, the first work function metal layer of each of the first and second transistors has a work function greater than that of the second work function metal layer, and the first transistor has a threshold voltage less than that of the second transistor.

[FIG. 1]